

Title (en)

SOLVENTLESS, RESISTLESS DIRECT DIELECTRIC PATTERNING

Title (de)

LÖSUNGSMITTELFREIES, RESISTLOSES DIREKTES STRUKTURIEREN VON DIELEKTRIKA

Title (fr)

FORMATION DIRECTE DES MOTIFS DE MATÉRIAUX DIELECTRIQUES SANS PHOTORÉSERVE ET SANS SOLVANT

Publication

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Application

EP 01904847 A 20010111

Priority

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Abstract (en)

[origin: WO0151990A1] Provided is a process for lithographically patterning a material on a substrate comprising the steps of (a) depositing a radiation sensitive material on the substrate by chemical vapor deposition; (b) selectively exposing the radiation sensitive material to radiation to form a pattern; and (c) developing the pattern using a supercritical fluid (SCF) as a developer. Also disclosed is a microstructure formed by the foregoing process. Also disclosed is a process for lithographically patterning a material on a substrate wherein after steps (a) and (b) above, the pattern is developed using a dry plasma etch. Also disclosed is a microstructure comprising a substrate; and a patterned dielectric layer, wherein the patterned dielectric layer comprises at least one two-dimensional feature having a dimensional tolerance more precise than 7%. Also disclosed is a microelectronic structure comprising a substrate; a plurality of transistors formed on the substrate; and a plurality of conductive features formed within a dielectric pattern, wherein the plurality of conductive features include at least one two-dimensional feature having a dimensional tolerance more precise than 7%.

IPC 8 full level

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